L	Hits	Search Text	DB	Time stamp
Number				
1	118	<pre>@ad&lt;=20010104 and 'amorphous silicon' same 'metal' same 'heating' with 'substrate'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/23 08:30
3	0	<pre>@ad&lt;=20010104 and 'amorphous silicon' same 'metal' near 'heating' with 'substrate'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/23 07:29
2	58	@ad<=20010104 and 'amorphous silicon' same 'metal' with 'heating' with 'substrate'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/23 07:29
4	0	<pre>@ad&lt;=20010104 and 'amorphous silicon' near 'metal' near 'heating' with 'substrate'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/23 07:29
5	52	<pre>@ad&lt;=20010104 and 'amorphous silicon' with 'metal' with 'heating' with 'substrate'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/23 07:55
6	1	<pre>@ad&lt;=20010104 and 'amorphous silicon' same 'sputtering' with 'metal' same 'simultaneously' same 'heating'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/23 07:45
7	1	<pre>@ad&lt;=20010104 and 'amorphous silicon' same 'sputtering' with 'metal' and 'simultaneously' same 'heating substrate'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/23 07:52
8	8	<pre>@ad&lt;=20010104 and 'amorphous silicon' and 'sputtering' with 'nickel' and 'heating' with 'simultaneously'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/23 07:52
9	0	<pre>@ad&lt;=20010104 and 'sputtering' with 'nickel' same 'heating substrate' with 'simultaneously'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/23 07:52
10	42	<pre>@ad&lt;=20010104 and 'sputtering' with 'metal' and 'simultaneously' same 'heating substrate'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/23
11	2	<pre>@ad&lt;=20010104 and 'sputtering' with 'metal' same 'simultaneously' same 'heating substrate'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/23 07:53
12	0	<pre>@ad&lt;=20010104 and 'amorphous silicon' with 'metal' with 'heating substrate' same 'simultaneously'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/23 07:55
13	0	<pre>@ad&lt;=20010104 and 'amorphous silicon' with 'metal' same 'heating substrate' same 'simultaneously'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/23 07:56
14	7	<pre>@ad&lt;=20010104 and 'amorphous silicon' with 'metal' and 'heating substrate' same 'simultaneously'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/23 08:14

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15	7	@ad<=20010104 and 'amorphous silicon'	USPAT;	2004/06/23
		with 'metal' and 'heating' adj1	US-PGPUB;	08:03
	ŀ	'substrate' same 'simultaneously'	EPO; JPO;	
			DERWENT;	
16	o	God-20010104 and In ail and Isnuttoni	IBM_TDB USPAT;	2004/06/23
1 10	١	@ad<=20010104 and 'a-si' and 'sputter'	US-PGPUB;	08:15
	ļ	<pre>near4 'metal' and 'heating substrate' same 'simultaneously'</pre>	EPO; JPO;	08:13
	ĺ	same simulcaneously	DERWENT;	
			IBM TDB	
17	0	@ad<=20010104 and 'a-si' and 'sputter'	USPAT;	2004/06/23
1 '	l "	same 'metal' and 'heating' with	US-PGPUB;	08:15
		'substrate' same 'simultaneously'	EPO; JPO;	00.13
		Substrace Same Simurcaneously	DERWENT;	
			IBM TDB	
18	26	@ad<=20010104 and 'a-si' and 'sputter'	USPAT;	2004/06/23
- "		same 'metal' and 'heating' with	US-PGPUB;	08:26
		'substrate'	EPO; JPO;	
			DERWENT;	
			IBM TDB	
21	195	<pre>@ad&lt;=20010104 and 'sputter' same 'nickel'</pre>	USPĀT;	2004/06/23
		and 'heating' with 'substrate'	US-PGPUB;	08:28
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
26	2	<pre>@ad&lt;=20010104 and 'sputter' same 'nickel'</pre>	USPAT;	2004/06/23
		with 'heating' with 'substrate'	US-PGPUB;	08:28
			EPO; JPO;	
			DERWENT;	
	71	0-d20010104 and lamaumhaus adlibrant	IBM_TDB USPAT;	2004/06/23
27	71	<pre>@ad&lt;=20010104 and 'amorphous silicon' same 'nickel' same 'heating' with</pre>	US-PGPUB;	08:30
		'substrate'	EPO; JPO;	00.30
		Substrate	DERWENT;	
	1		IBM TDB	
28	4	@ad<=20010104 and 'MILC' with 'nickel'	USPAT;	2004/06/23
= "	_		US-PGPUB;	09:35
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
29	6	@ad<=20010104 and 'MILC' same 'nickel'	USPAT;	2004/06/23
		•	US-PGPUB;	09:35
			EPO; JPO;	
			DERWENT;	
	1100		IBM_TDB	0000/04/11
_	1192	@ad<=20010104 and 'heating substrate' and	USPAT;	2003/04/11 13:46
		'amorphous silicon'	US-PGPUB; EPO; JPO;	13:46
			DERWENT;	
			IBM TDB	
_	943	((438/486) or (438/482)).CCLS.	USPAT;	2002/10/03
		( ( ( ( ( ( ( ( ( ( ( ( ( ( ( ( ( ( ( (	US-PGPUB;	13:05
			EPO; JPO;	
	1		DERWENT;	
	1		IBM_TDB	
[ -	71	(((438/486) or (438/482)).CCLS.) and	USPĀT;	2002/10/03
[	1	@ad<=20010104 and 'heating substrate' and	US-PGPUB;	13:00
	[	'amorphous silicon'	EPO; JPO;	
1			DERWENT;	
1			IBM_TDB	
-	2	(@ad<=20010104 and 'heating substrate'	USPAT;	2002/10/03
1		and 'amorphous silicon') and	US-PGPUB;	13:18
		@ad<=20010104 and 'heating substrate' and	EPO; JPO;	
1		'amorphous silicon' and MILC	DERWENT;	
<b> </b> _	2	(((438/486) or (438/482)).CCLS.) and MILC	IBM_TDB USPAT;	2002/10/03
-	1	and 'low temperature'	US-PGPUB;	13:36
1		and tow combetacate	EPO; JPO;	10.00
1			DERWENT;	
1			IBM TDB	
			·	

-	2	(@ad<=20010104 and 'heating substrate'	USPAT;	2002/10/03
		and 'amorphous silicon' ) and MILC and	US-PGPUB;	13:06
		'low temperature'	EPO; JPO;	
			DERWENT;	
			IBM_TDB	i
-	0	@ad<=20010104 and 'amorphous silicon'	USPAT;	2004/06/23
		with 'metal layer' and 'heating' with	US-PGPUB;	07:25
		'while depositing'	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	181	@ad<=20010104 and 'amorphous silicon'	USPAT;	2002/10/03
		with 'metal layer' and 'heating'	US-PGPUB;	13:11
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	109	(@ad<=20010104 and 'amorphous silicon'	USPAT;	2002/10/03
		with 'metal layer' and 'heating' ) and	US-PGPUB;	13:11
		'depositing'	EPO; JPO;	13.11
		depositing	DERWENT;	
			IBM TDB	
_	14	@ad<=20010104 and 'amorphous silicon'	USPAT;	2002/10/03
	"4	with 'metal layer' and 'heating' with	US-PGPUB;	13:11
	1	with 'metal layer' and 'heating' with   'depositing'	EPO; JPO;	10.11
		depositing		
			DERWENT;	l
	2	/And<-20010104 15	IBM_TDB	2002/10/24
-	2	(@ad<=20010104 and 'heating substrate'	USPAT;	2002/10/24
		and 'amorphous silicon') and	US-PGPUB;	13:10
		@ad<=20010104 and 'amorphous silicon' and	EPO; JPO;	!
		MILC	DERWENT;	
		/// 400 / 400	IBM_TDB	
-	303	(((438/486) or (438/482)).CCLS.) and 'low	USPAT;	2002/10/03
		temperature'	US-PGPUB;	13:37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	52	(((438/486) or (438/482)).CCLS.) and 'low	USPAT;	2002/10/03
		temperature' and 'heating substrate'	US-PGPUB;	13:37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	• • • • • • • • • • • • • • • • • • •	USPAT;	2002/10/24
		with depositing same metal and MILC	US-PGPUB;	13:51
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	58	@ad<=20010104 and MILC	USPĀT;	2004/06/22
			US-PGPUB;	13:55
			EPO; JPO;	
			DERWENT;	
•			IBM_TDB	
	0	@ad<=20010104 and heating adj1 substrate	USPĀT;	2002/10/24
		adj1 while same 'depositing metal'	US-PGPUB;	13:54
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	@ad<=20010104 and heat adj1 substrate	USPAT;	2002/10/24
		adj1 while same 'depositing metal'	US-PGPUB;	13:54
			EPO; JPO;	
	1		DERWENT;	
	,		IBM TDB	
_	3	@ad<=20010104 and heat adj1 substrate	USPAT;	2002/10/24
		same 'depositing metal'	US-PGPUB;	13:56
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	74	   @ad<=20010104 and heating adj1 substrate	USPAT;	2002/10/24
	'4	same 'depositing metal'	US-PGPUB;	14:15
1		same debosicing merar	EPO; JPO;	17.17
			DERWENT;	
1	I	I	IBM TDB	l

_	15	@ad<=20010104 and 'hot metallization'	USPAT; US-PGPUB; EPO; JPO;	2002/10/24 14:16
			DERWENT; IBM TDB	
-	191	@ad<=20010104 and 'amorphous silicon' same 'heating substrate'	USPAT; US-PGPUB; EPO; JPO;	2002/10/24 15:55
-	12	@ad<=20010104 and 'amorphous silicon' same 'heating substrate' same 'metal'	DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/10/24 15:40
_	3778	((438/149) or (438/158) or (438/315) or	EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/10/24
		(438/334) or (257/57)).CCLS.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	15:42
-	54	(((438/149) or (438/158) or (438/315) or (438/334) or (257/57)).CCLS.) and @ad<=20010104 and 'heating substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/24 15:56
-	2	"20020137310"	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/07 11:55
-	447	@ad<=20010104 and low adj temperature adj	DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/04/11 14:35
		-	EPO; JPO; DERWENT; IBM_TDB	
-	318928	(("257") or ("438")).CLAS.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/11
-	124	(@ad<=20010104 and low adj temperature adj crystallization ) and 'nickel'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/11 14:13
-	1	("6524662").PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/11 14:07
-	28	(@ad<=20010104 and low adj temperature adj crystallization ) and heat adj substrate and 'nickel'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/11 14:14
_	9	@ad<=20010104 and deposit adj nickel same 'heat' same 'substrate'	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/04/11 14:39
-	6	@ad<=20010104 and 'heated' with 'substrate' same deposit adj nickel	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/04/11 14:40
-	62	@ad<=20010104 and MILC	DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/11/07 11:26
			EPO; JPO; DERWENT; IBM TDB	11.20

	, <del></del> -			
-	3	("6524662").PN.	USPAT;	2003/11/07
			US-PGPUB;	11:22
			EPO; JPO;	İ
			DERWENT; IBM TDB	
_	24	@ad<=20010104 and Joo-seung.in.	USPAT;	2003/11/07
	44	eau\-20010104 and 000 Seung.in.	US-PGPUB;	11:27
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	39	Joo-seung-ki.in.	USPAT;	2003/11/07
			US-PGPUB;	11:27
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	("6097037").PN.	USPAT;	2003/11/07
			US-PGPUB;	11:57
			EPO; JPO;	
			DERWENT;	
	001	8-4-20010104 and lamambana ailiaant	IBM_TDB	2002/11/07
-	231	<pre>@ad&lt;=20010104 and 'amorphous silicon' same 'nickel' same 'sputtering'</pre>	USPAT; US-PGPUB;	2003/11/07 12:02
		same urcyer same spuccering.	EPO; JPO;	14.04
			DERWENT;	
			IBM TDB	
_	53	@ad<=20010104 and 'amorphous silicon'	USPAT;	2003/11/07
		with 'nickel' with 'sputtering'	US-PGPUB;	12:19
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	8	@ad<=20010104 and 'amorphous silicon'	USPAT;	2003/11/07
		with 'nickel' with 'sputtering' with	US-PGPUB;	12:22
		'temperature'	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	222	@ad<=20010104 and 'sputtering' with	USPAT;	2003/11/07
		'temperature' same 'nickel'	US-PGPUB;	12:22
			EPO; JPO;	]
			DERWENT;	
	100		IBM_TDB	2003/11/07
-	100	<pre>@ad&lt;=20010104 and 'sputtering' with 'temperature' with 'nickel'</pre>	USPAT; US-PGPUB;	12:27
		remberarare with Hicker	EPO; JPO;	14.41
			DERWENT;	
			IBM TDB	
_	5	@ad<=20010104 and 'nickel' with	USPAT;	2003/11/07
		'sputtering temperature'	US-PGPUB;	12:49
		• • • • • • • • • • • • • • • • • • • •	EPO; JPO;	
			DERWENT;	
			IBM_TDB	]
-	0	@ad<=20010104 and 'nickel' with	USPAT;	2003/11/07
		'oxidation' adj1 'stable' with 'silicide'	US-PGPUB;	12:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	6	@ad<=20010104 and 'nickel' with	USPAT;	2003/11/07
1		'oxidation' adj1 'stable'	US-PGPUB;	12:48
			EPO; JPO;	
			DERWENT;	
	11	0.d<-20010104 and Initiality	IBM_TDB USPAT;	2003/11/07
-	11	@ad<=20010104 and 'nickel' same   'sputtering temperature'	US-PGPUB;	12:55
		spaceting cemperacure	EPO; JPO;	*2.33
	1		DERWENT;	
1			IBM TDB	
-	93	@ad<=20010104 and 'nickel' same	USPAT;	2003/11/07
		'oxidation temperature'	US-PGPUB;	12:56
			EPO; JPO;	
			DERWENT;	
L	<u> </u>		IBM_TDB	
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	21	10-4 < 20010104 and Initialized	TIGDAM.	1 2002 /11 /07
_	31	@ad<=20010104 and 'nickel' with	USPAT;	2003/11/07 13:02
		'oxidation temperature'	US-PGPUB;	13:02
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/11/07
-	72		USPAT;	2003/11/07
		'silicidation'	US-PGPUB;	13:02
!	<u> </u>		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	27	1	USPAT;	2003/11/07
		'silicidation'	US-PGPUB;	13:04
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	26	1 *	USPAT;	2003/11/07
		'silicidation' and 'temperature'	US-PGPUB;	13:04
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
<b>]</b> -	17		USPAT;	2003/11/07
		'silicidation' same 'temperature'	US-PGPUB;	13:15
		-	EPO; JPO;	
}			DERWENT;	
1			IBM TDB	
_	153	<pre>@ad&lt;=20010104 and 'nickel' same 'silicon'</pre>	USPAT;	2003/11/07
		with 'crystallized' same 'temperature'	US-PGPUB;	13:16
			EPO; JPO;	
			DERWENT;	
	1		IBM TDB	1
_	64	<pre>@ad&lt;=20010104 and 'nickel' same 'silicon'</pre>	USPAT;	2003/11/07
		with 'crystallized' with 'temperature'	US-PGPUB;	13:16
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	("5614291").PN.	USPAT;	2003/11/07
		,, ,	US-PGPUB;	13:22
			EPO; JPO;	
			DERWENT;	
]			IBM TDB	
_	2	"20020137310"	USPAT;	2004/06/22
	1		US-PGPUB;	13:14
			EPO; JPO;	'
			DERWENT;	
			IBM TDB	
l _	12	@ad<=20010104 and MILC and 'nickel'	USPAT;	2004/06/23
		Caa . 2002020 and man manua	US-PGPUB;	09:34
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
L	<u> </u>	<u></u>	1	